

Product Overview

FFSH20120ADN-F085: SiC, Dual Die, 1200 V, 20 A

For complete documentation, see the data sheet.

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size & cost

Features

- Max Junction Temperature 175 °C
- Avalanche Rated 100 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery / No Forward Recovery
- AEC-Q101 qualified

Applications

- Automotive HEV-EV Onboard Chargers
- Automotive HEV-EV DC-DC Converters

End Products

- Automotive HEV-EV Onboard Chargers

Part Electrical Specifications

Product	Compliance	Status	Device Grade	Configuration	V _{RRM} (V)	I _{F(ave)} (A)	V _F (Max)	I _{FSM} (A)	I _R (Max) (μA)	Package Type
FFSH20120ADN-F085	AEC Qualified PPAP Capable Pb-free Halide free	Active		Dual Common Cathode	1200V	10A	1.75V	96A	200uA	TO-247-3

For more information please contact your local sales support at www.onsemi.com.

Created on: 12/9/2018